

JST24F-800CW 25A TRIAC

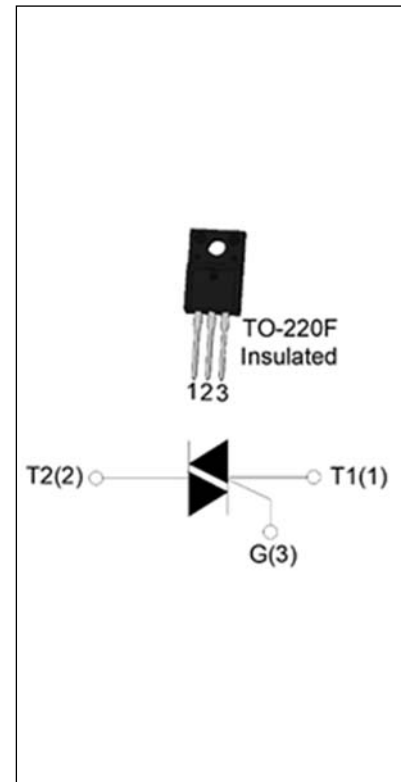
Rev.A.1.1

DESCRIPTION:

The JST24F-800CW triac is suitable for general purpose AC switching. It can be used as an ON/OFF function in applications such as heating regulation, induction motor starting circuits, for phase control operation in light dimmers, motor speed controllers. JST24F-800CW snubberless triac is especially recommended for use on inductive loads. By using an external plastic package, JST24F-800CW provides a rated insulation voltage of 2000 VRMS, complying with UL standards (File ref: E252906). Package TO-220F is RoHS compliant.

MAIN FEATURES

Symbol	Value	Unit
$I_{T(RMS)}$	25	A
V_{DRM}/V_{RRM}	800	V
$I_{GT\ I/II/III}$	35/35/35	mA



ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Storage junction temperature range	T_{stg}	-40-150	°C
Operating junction temperature range	T_j	-40-125	°C
Repetitive peak off-state voltage ($T_j=25^\circ\text{C}$)	V_{DRM}	800	V
Repetitive peak reverse voltage ($T_j=25^\circ\text{C}$)	V_{RRM}	800	V
RMS on-state current ($T_c \leq 72^\circ\text{C}$)	$I_{T(RMS)}$	25	A
Non repetitive surge peak on-state current (full cycle , $t_p=20\text{ms}$, $T_j=25^\circ\text{C}$)	I_{TSM}	250	A
Non repetitive surge peak on-state current (full cycle , $t_p=16.6\text{ms}$, $T_j=25^\circ\text{C}$)		275	
I^2t value for fusing ($t_p=10\text{ms}$, $T_j=25^\circ\text{C}$)	I^2t	340	A^2s
Critical rate of rise of on-state current ($I_G=2 \times I_{GT}$, $f=100\text{Hz}$, $T_j=125^\circ\text{C}$)	di/dt	100	$\text{A}/\mu\text{s}$
Peak gate current ($t_p=20\mu\text{s}$, $T_j=125^\circ\text{C}$)	I_{GM}	4	A
Average gate power dissipation ($T_j=125^\circ\text{C}$)	$P_{G(AV)}$	0.5	W

Peak gate power	P_{GM}	10	W
Peak pulse voltage ($T_j=25^{\circ}\text{C}$; non-repetitive, off-state; FIG.7)	V_{pp}	2.5	kV

ELECTRICAL CHARACTERISTICS ($T_j=25^{\circ}\text{C}$ unless otherwise specified)

Symbol	Test Condition	Quadrant	Value		Unit
I_{GT}	$V_D=12\text{V}$ $R_L=33\Omega$	I - II -III	MAX.	35	mA
V_{GT}		I - II -III	MAX.	1	V
V_{GD}	$V_D=V_{DRM}$ $T_j=125^{\circ}\text{C}$ $R_L=3.3\text{k}\Omega$	I - II -III	MIN.	0.2	V
I_L	$I_G=1.2I_{GT}$	I -III	MAX.	70	mA
		II		80	
I_H	$I_T=500\text{mA}$		MAX.	50	mA
dV/dt	$V_D=540\text{V}$ Gate Open $T_j=125^{\circ}\text{C}$		MIN.	1200	V/ μs
$(dI/dt)_c$	$(dV/dt)_c=20\text{V}/\mu\text{s}$ $T_j=125^{\circ}\text{C}$		MIN.	15	A/ms
t_{on}	$I_G=40\text{mA}$ $I_A=200\text{mA}$ $I_R=20\text{mA}$ $T_j=25^{\circ}\text{C}$		TYP.	7	μs
t_{off}				50	

STATIC CHARACTERISTICS

Symbol	Parameter		Value(MAX.)	Unit
V_{TM}	$I_{TM}=35\text{A}$ $t_p=380\mu\text{s}$	$T_j=25^{\circ}\text{C}$	1.5	V
V_{TO}	Threshold voltage	$T_j=125^{\circ}\text{C}$	0.75	V
R_D	Dynamic resistance	$T_j=125^{\circ}\text{C}$	18	$\text{m}\Omega$
I_{DRM}	$V_D=V_{DRM}$ $V_R=V_{RRM}$	$T_j=25^{\circ}\text{C}$	5	μA
I_{RRM}		$T_j=125^{\circ}\text{C}$	2	mA

THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
$R_{th(j-c)}$	junction to case (AC)	1.5	$^{\circ}\text{C}/\text{W}$
$R_{th(j-a)}$	junction to ambient (AC)	60	$^{\circ}\text{C}/\text{W}$

ORDERING INFORMATION

	J	ST	24	F	-800	CW
JieJie Microelectronics Co., Ltd.	Triacs	$I_{T(RMS)}: 25A$				
			F: TO-220F(Ins)			CW: $I_{GT1-3} \leq 35mA$
					800: $V_{DRM} / V_{RRM} \geq 800V$	

MARKING

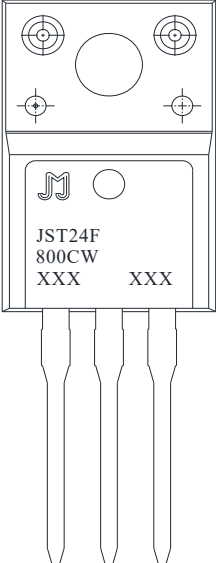
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FIG.1: Maximum power dissipation versus RMS on-state current

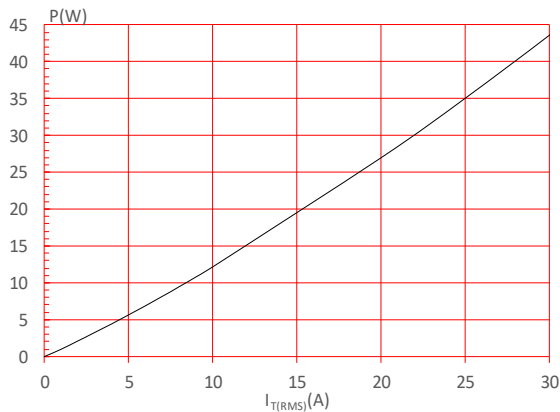


FIG.3: Surge peak on-state current versus number of cycles

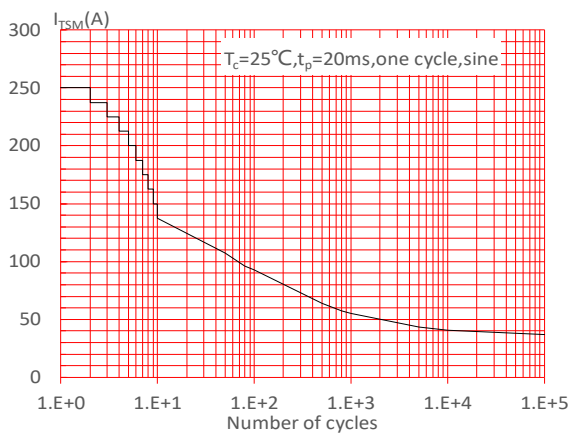


FIG.5: Non-repetitive surge peak on-state current for a sinusoidal pulse with width $t_p < 20\text{ms}$, and corresponding value of I^2t ($di/dt < 100\text{A}/\mu\text{s}$)

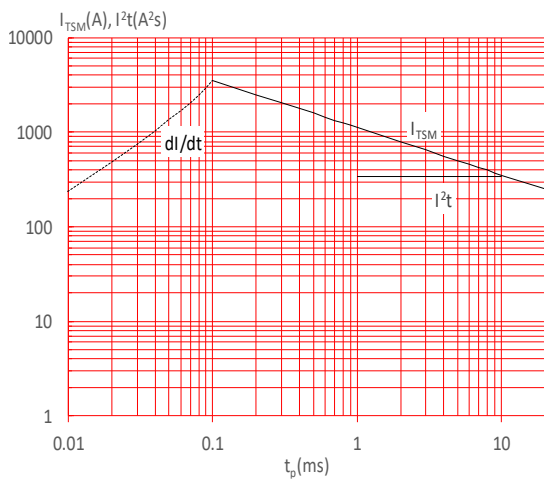


FIG.2: RMS on-state current versus case temperature

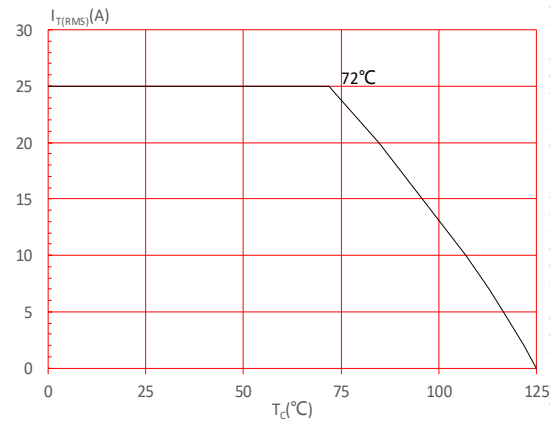


FIG.4: On-state characteristics

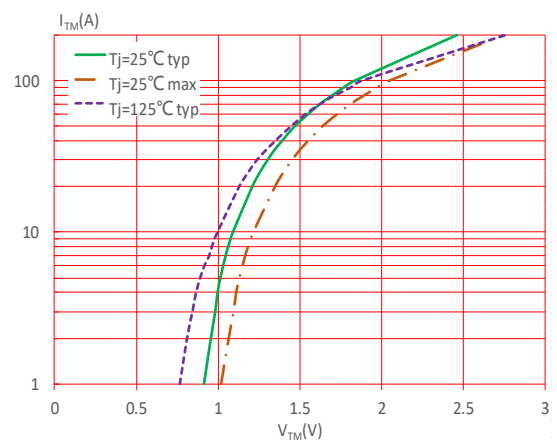


FIG.6: Relative variations of gate trigger current, holding current and latching current versus junction temperature

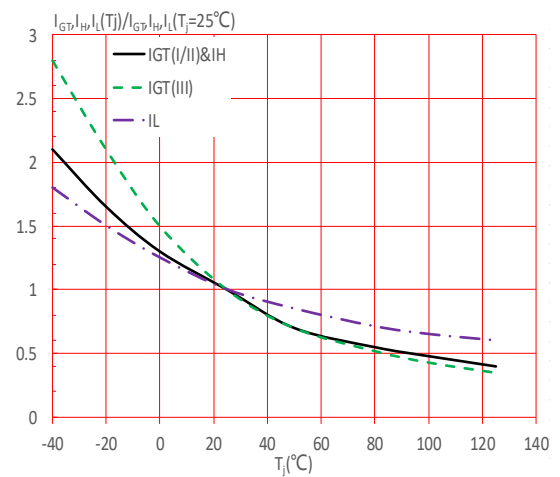
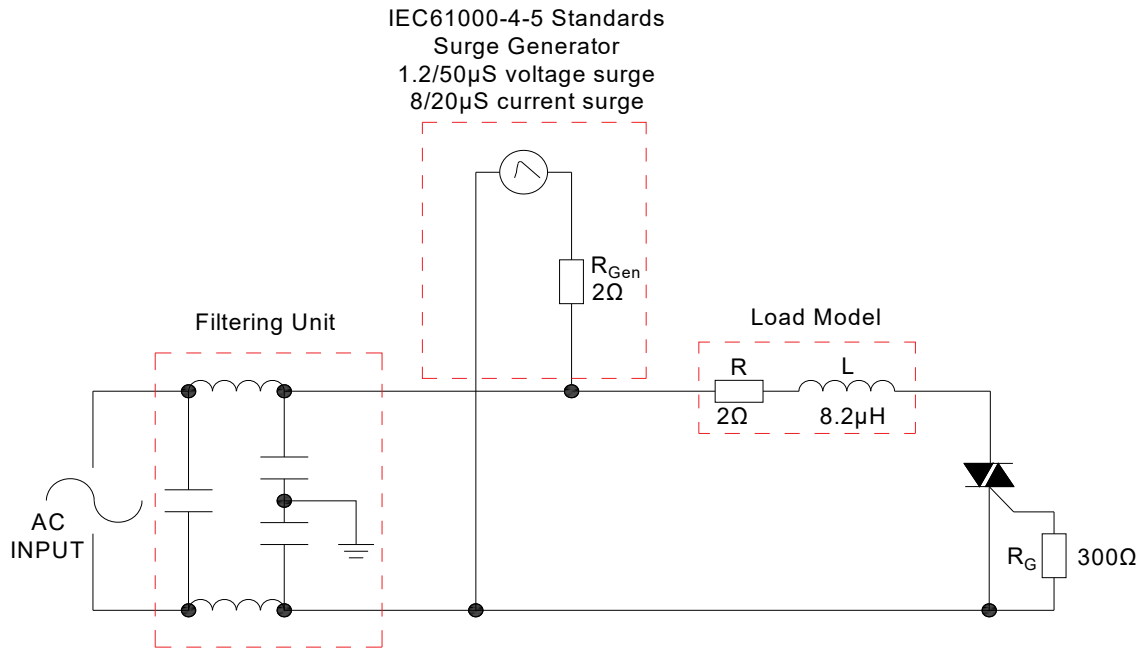


FIG.7: Test circuit for inductive and resistive loads to IEC-61000-4-5 standards



LEAD FORMING AND SOLDERING

Refer to the application note “Assembly Instructions for Thyristors in Through-hole Package” released by JieJie Microelectronics.

ORDERING INFORMATION

Order code	Voltage $V_{\text{DRM}}/V_{\text{RRM}}$ (V)	IGT(mA)	Package	Base qty. (pcs)	Delivery mode
		I - II - III			
JST24F-800CW	800	35	TO-220F(Ins)	50	Tube

Document Revision History

Date	Revision	Changes
Apr.12, 2023	A.1.0	Last updated
Oct.13, 2025	A.1.1	Revise PACKAGE MECHANICAL DATA

Technical drawing of a 3-pronged electrical plug. The drawing includes a top view and a side view. The top view shows a rectangular body with two circular prongs and a central grounding pin. Dimensions include overall width E , prong width I , prong length $L1$, prong diameter $\phi 3.05-3.25mm$, and body width $L3$. The side view shows the plug's profile with dimensions A (top flange thickness), $C2$ (top flange width), F (body height), D (body diameter), $C3$ (body width), C (pin diameter), and K (pin length). A chamfer angle N is indicated on the side view. The bottom view shows the plug's base with dimensions H (total height), $L2$ (prong spacing), J (prong length), G (base width), B (base diameter), and M (prong diameter).

The technical drawing illustrates the design of a three-needle embroidery machine head assembly through three distinct views:

- Front View (Left):** Shows the top profile of the machine head. It features two circular mounting holes on the left side, separated by a distance of 520 ± 0.5 . The overall width of the assembly is 530 ± 0.5 . A central section houses three vertical needles.
- Side View (Middle):** Provides a side profile of the machine head. It highlights a "printing area" located at a height of 3 units from the base. A horizontal dimension of 80 units is shown between the printing area and a circular feature. This circular feature has a diameter of $\phi 4.5$ and is positioned at a height of 5.5 units. Another circular feature at the bottom right has a diameter of $\phi 3.0 \pm 0.05$.
- Cross-sectional View (Right):** Details the internal structure of the machine head. It shows a total height of 33 units. Key internal dimensions include a top layer thickness of 7.0 units, a middle section thickness of 2.4 units, a gap of 3.8 units, and a bottom section thickness of 0.6 units. The overall width of the cross-section is 18.0 units.

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